I. Introduction

1 Overview

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Dynac G310 PCIe 3x4 SSD is a high performance and high reliability storage device based on NAND Flash technology designed to solve the bottleneck of computing system by traditional hard disk drives.

Dynac G310 is a good storage device for NB and Tabletop PC.

Dynac G310 PCIe 3x4 SSD purely consists of semiconductor devices and NAND flash memories, which give rugged features against shock and vibration, used in extreme environment such as industrial PC to increase MTBF. Furthermore, Our PCIE SSD has highly advanced flash memory management algorithm to guarantee.

2 Part Type Introduction

This chapter is about the specifications of the M.2 2280 PCIe Solid State Drive with PCIe 3.0 interface.

Туре	Capacity	Flash	Interface
G310	256GB-1TB	3D TLC	M.2 NVMe

Table 1 Capacity Specifications

Capacity	Available Capacity	CDM R / W (MB/s)	CDM Random R / W (IOPS)
256GB	238.47GB	2100/1000	5983/64627
512GB	476.94GB	2400/1600	188008/78161
1TB	953.86GB	2400/1800	190681/166029

II. Product Specifications

2.1 Physical Dimensions

Parameter	Value
Length	80 mm
width	22 mm

height 0.8+0.1 mm

Table 2 Physical dimensions of the driver

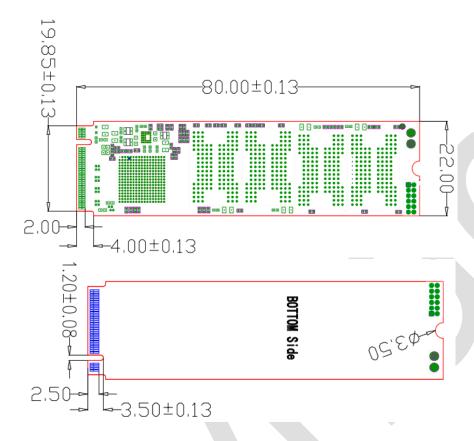


Figure 1 Physical dimensions

2.2 Interface Specification

2.2.1 Interface Mode

- Supports 4 flash channels with 4 chip enable (CE) pins per channel
- Supports ONFI 4.0/3.0 and Toggle 3.0/2.0 interface, frequency up to 667 MT/s
- Supports Asynchronous SDR, Synchronous DDR and Toggle DDR NAND
- Supports Flash I/O power 1.8V/1.2V operation
- Multi-plane operation
- Programmable driving strength fits different types of NAND configurations

Based spec	Interface	M.2 NVMe
	Dimension	80*22*0.8 mm
	Weight ①	5.6g
	Capacity	256GB-1TB

Controller SMI2263XT Flash typ 3D TLC NAND Flash ASSD Sequential Read Up to 2000MB/s ASSD Sequential Write Up to 1500MB/s ATTO Sequential Read Up to 2300MB/s ATTO Sequential Write Up to 1600MB/s ATTO Sequential Write Up to 1600MB/s ATTO Sequential Write Up to 1600MB/s Standby 3.3V±5% Standby 11.5mW Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited MTBF: >1,000,000 hours
ASSD Sequential Read Up to 2000MB/s ASSD Sequential Write Up to 1500MB/s ATTO Sequential Read Up to 2300MB/s ATTO Sequential Write Up to 1600MB/s ATTO Sequential Write Up to 1600MB/s Power Supply 3.3V±5% Standby 11.5mW Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited
ASSD Sequential Write Up to 1500MB/s ATTO Sequential Read Up to 2300MB/s ATTO Sequential Write Up to 1600MB/s Power Supply 3.3V±5% Standby 11.5mW Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited
Read/Write Performance ② ATTO Sequential Read Up to 2300MB/s ATTO Sequential Write Up to 1600MB/s Power Supply 3.3V±5% Standby 11.5mW Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited
ATTO Sequential Read
Power Supply 3.3V±5% Standby 11.5mW Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited
Standby
Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited
Maximum Ripple 70 mV(peak to peak) 4KB Random Write 2.5W TBW(endurance): 80-320TBW Read endurance: unlimited
TBW(endurance): 80-320TBW Read endurance: unlimited
Read endurance: unlimited
MTBF: >1,000,000 hours
Data retention: >20years @ 25°C
Data destroy do not support
Reliability Sudden power-off recovery support
S.M.A.R.T,NCQ,Trim and dynamic power management support
Static and dynamic wear-leveling
Bad block management algorithm
ECC: LDPC ECC
Storage temperature: -55~95 ℃
Operation temperature: 0~75℃
Environment Humidity: 5%~95%
Vibration 15G (10 to 2000Hz)
Shock 350G at 0.5ms
Warranty 3 years

III. Ordering Information

Model	Capacity	PN
	256GB	G310256GB/R
G310	512GB	G310512GB/R
	1TB	G3101TB/R